**Product data sheet** 

## 1. General description

PNP low  $V_{CEsat}$  transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4041NZ

### 2. Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  $I_C$  and  $I_{CM}$
- · High collector current gain (hFE) at high IC
- · High energy efficiency due to less heat generation
- · Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

## 3. Applications

- Loadswitch
- · Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-60	٧
I <sub>C</sub>	collector current		-	-	-5.7	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-15	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -5 A; $I_B$ = -500 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	29	43.5	mΩ



60 V, 5.7 A PNP low VCEsat transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	C
2	С	collector		В
3	E	emitter		P
4	С	collector	1 2 3	Ė
			SC-73 (SOT223)	sym028

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package					
	Name	Description	Version			
PBSS4041PZ		plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body	SOT223			

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBSS4041PZ	PB4041
	PZ

60 V, 5.7 A PNP low VCEsat transistor

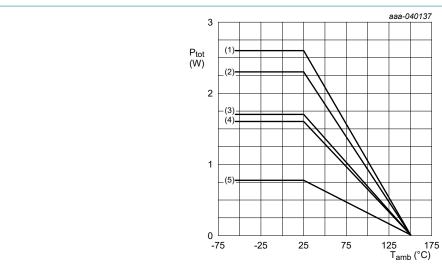
## 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-60	V
$V_{CEO}$	collector-emitter voltage	open base		-	-60	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current			-	-5.7	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-15	А
I <sub>B</sub>	base current			-	-1	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.77	W
			[2]	-	1.7	W
			[3]	-	1.6	W
			[4]	-	2.3	W
			[5]	-	2.6	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, 4-layer, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer, tin-plated, mounting pad for collector 1 cm<sup>2</sup>
- $[5] \quad \text{Device mounted on a ceramic PCB, Al}_2\text{O}_3, \text{ single-sided, 35} \ \mu\text{m copper, tin-plated and standard footprint.}$



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, single-sided, 35 µm copper, standard footprint
- (2) FR4 PCB, 4-layer copper, 1 cm<sup>2</sup>
- (3) FR4 PCB, single-sided, 35 µm copper, 6 cm<sup>2</sup>
- (4) FR4 PCB, 4-layer copper, standard footprint
- (5) FR4 PCB, single-sided, 35 µm copper, standard footprint

Fig. 1. Power derating curves

PBSS4041PZ

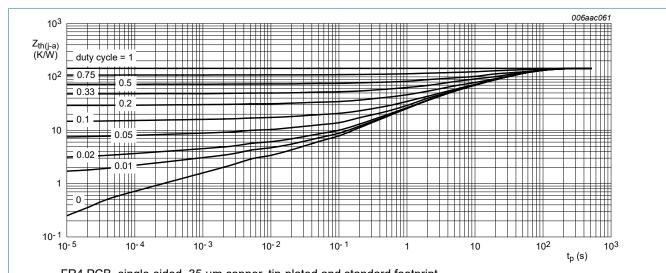
60 V, 5.7 A PNP low VCEsat transistor

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

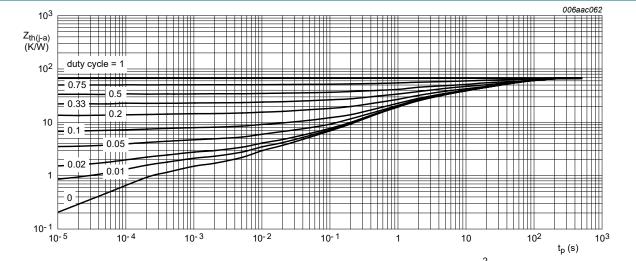
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance fr junction to ambient	thermal resistance from	]	[1]	-	-	160	K/W
	junction to ambient		[2]	-	-	75	K/W
			[3]	-	-	80	K/W
			[4]	-	-	55	K/W
			[5]	-	-	50	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	11	K/W

- [1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, 4-layer, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, 4-layer, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [5] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, single-sided, 35 μm copper, tin-plated and standard footprint.



FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint

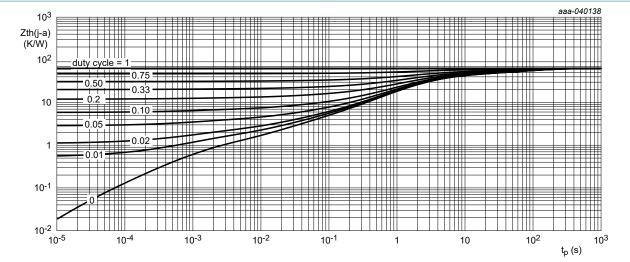
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>

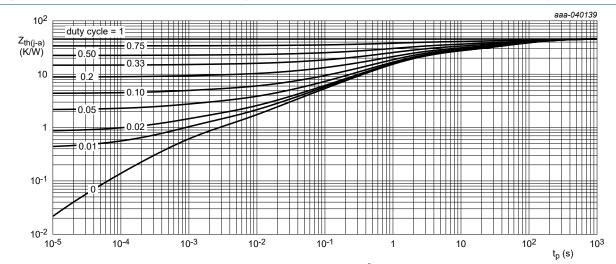
Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 60 V, 5.7 A PNP low VCEsat transistor



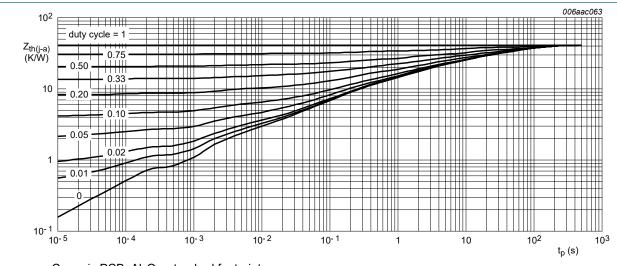
FR4 PCB, 4-layer, tin-plated and standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, 4-layer, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, 5.7 A PNP low VCEsat transistor

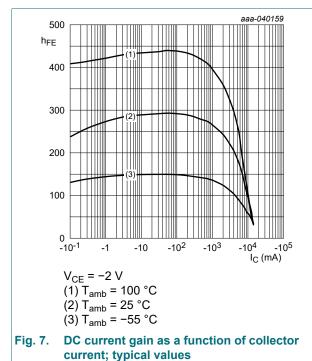
## 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = -100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	-60	-	-	V
/ <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C = -10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-60	-	-	V
/ <sub>(BR)EBO</sub>	emitter-base breakdown voltage	$I_E = -100 \ \mu A; I_C = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	-5	-	-	V
СВО	collector-base cut-off	V <sub>CB</sub> = -60 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	$V_{CB} = -60 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$	-	-	-55	μΑ
CES	collector-emitter cut-off current	$V_{CE} = -48 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
EBO	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
) <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = -500 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	200	300	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	200	285	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -2 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	200	265	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -4 A; pulsed; $t_{p} \le$ 300 µs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	150	225	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -6 A; pulsed; $t_{p} \le$ 300 µs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	120	190	-	
/ <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -1 A; $I_B$ = -10 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-85	-125	mV
		$I_C$ = -1 A; $I_B$ = -50 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-50	-63	mV
		$I_C$ = -2 A; $I_B$ = -40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-110	-150	mV
		$I_C$ = -4 A; $I_B$ = -200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-125	-195	mV
		$I_C$ = -4 A; $I_B$ = -400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-105	-175	mV
		$I_C$ = -6 A; $I_B$ = -300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-180	-285	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -5 A; $I_B$ = -500 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	29	43.5	mΩ
/ <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-0.8	-0.9	V
		$I_C$ = -4 A; $I_B$ = -400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-0.92	-1.05	V
/ <sub>BE</sub>	base-emitter voltage	$V_{CE}$ = -2 V; $I_{C}$ = -2 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-0.75	-0.85	V

### 60 V, 5.7 A PNP low VCEsat transistor

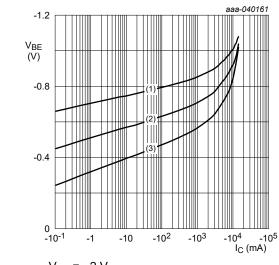
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>d</sub>	delay time	$V_{CC}$ = -12.5 V; $I_{C}$ = -1 A; $I_{Bon}$ = -50 mA; $I_{Boff}$ = 50 mA; $T_{amb}$ = 25 °C	-	60	-	ns
t <sub>r</sub>	rise time		-	50	-	ns
t <sub>on</sub>	turn-on time		-	110	-	ns
t <sub>s</sub>	storage time		-	550	-	ns
t <sub>f</sub>	fall time		-	70	-	ns
t <sub>off</sub>	turn-off time		-	620	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	75	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_E$ = 0 A; $I_e$ = 0 A; $I_e$ = 1 MHz; $I_{Amb}$ = 25 °C	-	120	-	pF



aaa-040160 -15 I<sub>B</sub> (mA) = -120 I<sub>C</sub> (A) -96 -12 -60 -9 -36 -6 -24 -3 -4 V<sub>CE</sub> (V) -1 -2 -3  $T_{amb}$  = 25 °C

Fig. 8. Collector current as a function of collectoremitter voltage; typical values

#### 60 V, 5.7 A PNP low VCEsat transistor



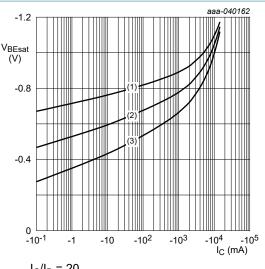
$$V_{CE} = -2 V$$

$$(1) T_{amb} = -55 °C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 9. Base-emitter voltage as a function of collector current; typical values



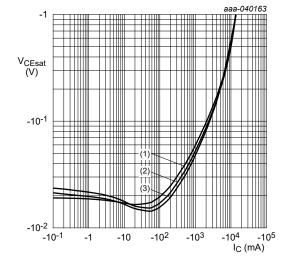
$$I_C/I_B = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values



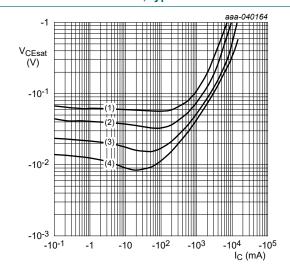
 $I_{\rm C}/I_{\rm B} = 20$ 

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

$$(2) T_{omb} = 25 ^{\circ}C$$

(2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -55 °C

Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

 $(1) I_C/I_B = 100$ 

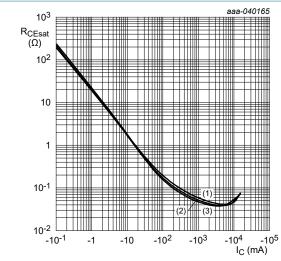
(2)  $I_C/I_B = 50$ 

(3)  $I_C/I_B = 20$ 

(4)  $I_C/I_B = 10$ 

Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values

#### 60 V, 5.7 A PNP low VCEsat transistor



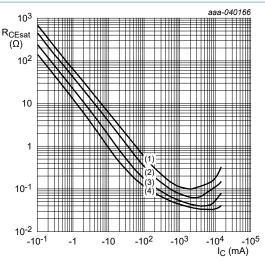
$$I_{\rm C}/I_{\rm B} = 20$$

$$I_C/I_B = 20$$
  
(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2) 
$$T_{amb} = 25 \,^{\circ}\text{C}$$
  
(3)  $T_{amb} = -55 \,^{\circ}\text{C}$ 

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 13. Collector-emitter saturation resistance as a function of collector current; typical values



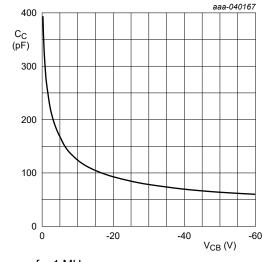
$$T_{amb} = 25 \, ^{\circ}C$$

(1) 
$$I_C/I_B = 100$$

$$(2) I_{\rm C}/I_{\rm B} = 50$$

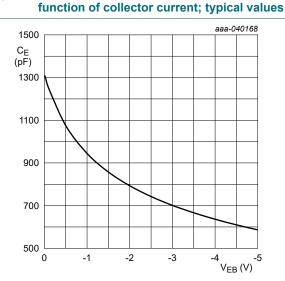
(3) 
$$I_C/I_B = 20$$

 $(3) I_{\rm C}/I_{\rm B} = 10$ Fig. 14. Collector-emitter saturation resistance as a



f = 1 MHz; $T_{amb} = 25^{\circ} C$ 

Fig. 15. Collector capacitance as a function of collector- Fig. 16. Emitter capacitance as a function of emitterbase voltage; typical values

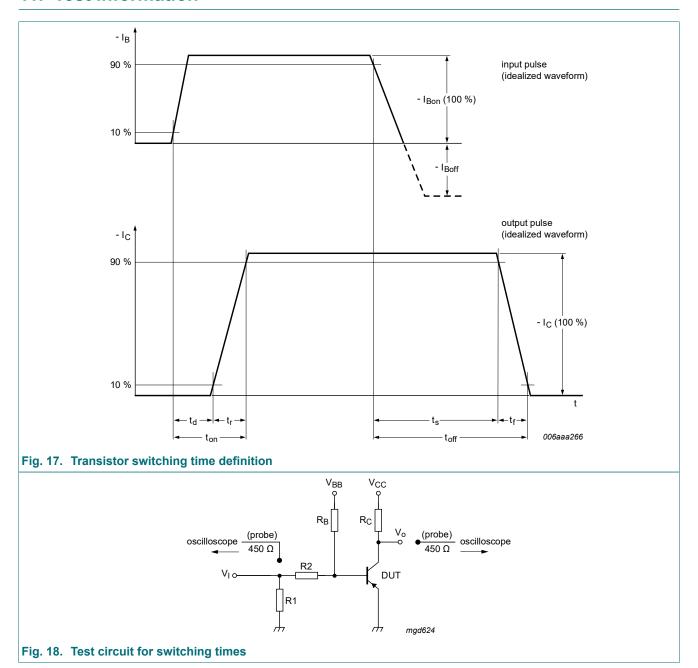


f = 1 MHz; $T_{amb} = 25 \, ^{\circ}C$ 

base voltage; typical values

60 V, 5.7 A PNP low VCEsat transistor

## 11. Test information

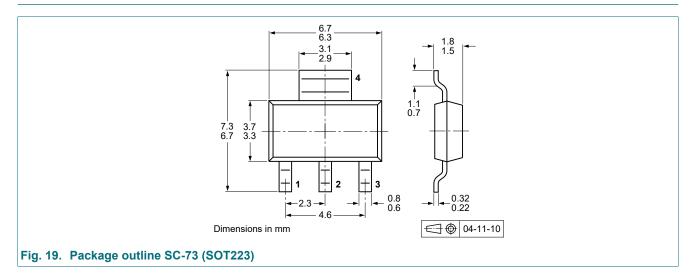


### **Quality information**

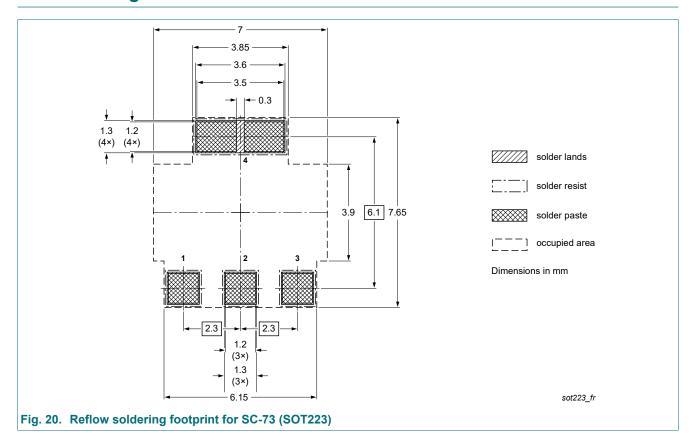
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

60 V, 5.7 A PNP low VCEsat transistor

## 12. Package outline

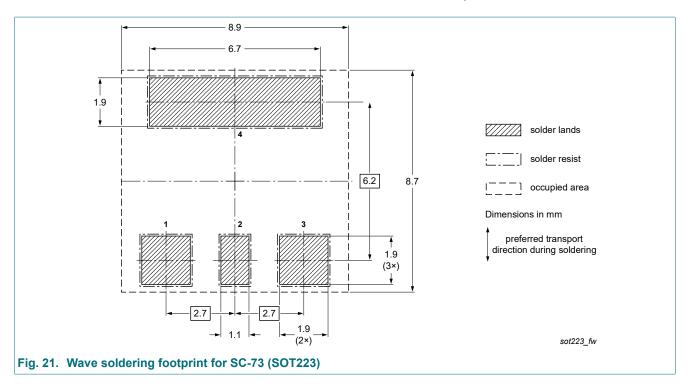


## 13. Soldering



**Product data sheet** 

### 60 V, 5.7 A PNP low VCEsat transistor



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# 14. Revision history

#### **Table 8. Revision history**

Table 6. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS4041PZ v.2	20240920	Product data sheet	-	PBSS4041PZ_1		
Modifications:		<ul><li>Section "Packing information" removed.</li><li>New graphics added, graphs updated and values changed.</li></ul>				
PBSS4041PZ_1	20100331	Product data sheet	-	-		

#### 60 V, 5.7 A PNP low VCEsat transistor

### 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <a href="https://www.nexperia.com">https://www.nexperia.com</a>.

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PBSS4041PZ

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### 60 V, 5.7 A PNP low VCEsat transistor

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 20 September 2024

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